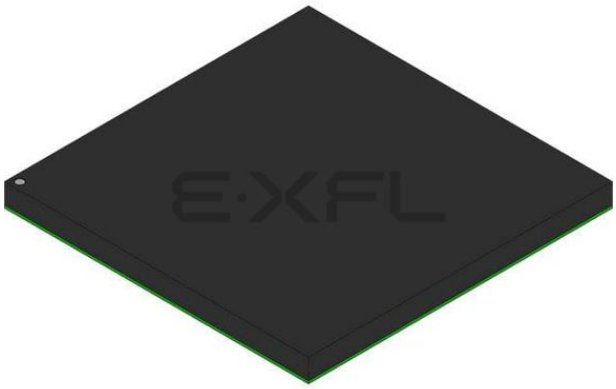

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	683
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	956-BBGA
Supplier Device Package	956-BGA (40x40)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep1s80b956c6n

2. Stratix Architecture

S51002-3.2

Functional Description

Stratix® devices contain a two-dimensional row- and column-based architecture to implement custom logic. A series of column and row interconnects of varying length and speed provide signal interconnects between logic array blocks (LABs), memory block structures, and DSP blocks.

The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device.

M512 RAM blocks are simple dual-port memory blocks with 512 bits plus parity (576 bits). These blocks provide dedicated simple dual-port or single-port memory up to 18-bits wide at up to 318 MHz. M512 blocks are grouped into columns across the device in between certain LABs.

M4K RAM blocks are true dual-port memory blocks with 4K bits plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 291 MHz. These blocks are grouped into columns across the device in between certain LABs.

M-RAM blocks are true dual-port memory blocks with 512K bits plus parity (589,824 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 144-bits wide at up to 269 MHz. Several M-RAM blocks are located individually or in pairs within the device's logic array.

Digital signal processing (DSP) blocks can implement up to either eight full-precision 9 × 9-bit multipliers, four full-precision 18 × 18-bit multipliers, or one full-precision 36 × 36-bit multiplier with add or subtract features. These blocks also contain 18-bit input shift registers for digital signal processing applications, including FIR and infinite impulse response (IIR) filters. DSP blocks are grouped into two columns in each device.

Each Stratix device I/O pin is fed by an I/O element (IOE) located at the end of LAB rows and columns around the periphery of the device. I/O pins support numerous single-ended and differential I/O standards. Each IOE contains a bidirectional I/O buffer and six registers for registering input, output, and output-enable signals. When used with

TriMatrix memory architecture can implement pipelined RAM by registering both the input and output signals to the RAM block. All TriMatrix memory block inputs are registered providing synchronous write cycles. In synchronous operation, the memory block generates its own self-timed strobe write enable (WREN) signal derived from the global or regional clock. In contrast, a circuit using asynchronous RAM must generate the RAM WREN signal while ensuring its data and address signals meet setup and hold time specifications relative to the WREN signal. The output registers can be bypassed. Flow-through reading is possible in the simple dual-port mode of M512 and M4K RAM blocks by clocking the read enable and read address registers on the negative clock edge and bypassing the output registers.

Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The Quartus II software automatically implements larger memory by combining multiple TriMatrix memory blocks. For example, two 256 × 16-bit RAM blocks can be combined to form a 256 × 32-bit RAM block. Memory performance does not degrade for memory blocks using the maximum number of words available in one memory block. Logical memory blocks using less than the maximum number of words use physical blocks in parallel, eliminating any external control logic that would increase delays. To create a larger high-speed memory block, the Quartus II software automatically combines memory blocks with LE control logic.

Clear Signals

When applied to input registers, the asynchronous clear signal for the TriMatrix embedded memory immediately clears the input registers. However, the output of the memory block does not show the effects until the next clock edge. When applied to output registers, the asynchronous clear signal clears the output registers and the effects are seen immediately.

Parity Bit Support

The memory blocks support a parity bit for each byte. The parity bit, along with internal LE logic, can implement parity checking for error detection to ensure data integrity. You can also use parity-size data words to store user-specified control bits. In the M4K and M-RAM blocks, byte enables are also available for data input masking during write operations.

Table 2–12 shows the input and output data signal connections for the column units (B1 to B6 and A1 to A6). It also shows the address and control signal input connections to the row units (R1 to R11).

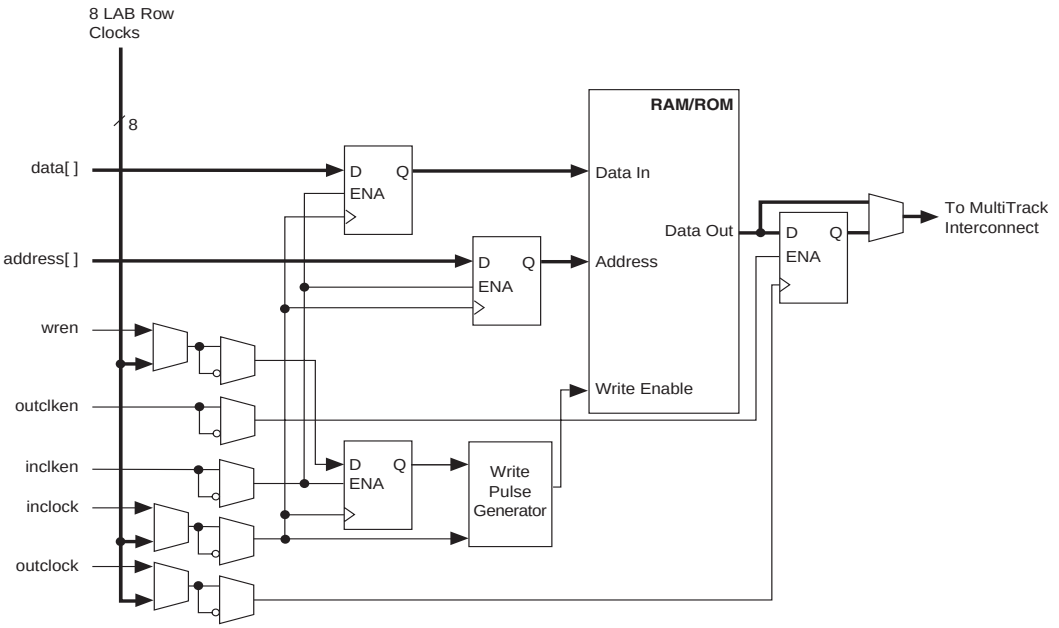
Table 2–12. M-RAM Row & Column Interface Unit Signals

Unit Interface Block	Input SIgnals	Output Signals
R1	addressa[7..0]	
R2	addressa[15..8]	
R3	byte_enable_a[7..0] renwe_a	
R4	-	
R5	-	
R6	clock_a clocken_a clock_b clocken_b	
R7	-	
R8	-	
R9	byte_enable_b[7..0] renwe_b	
R10	addressb[15..8]	
R11	addressb[7..0]	
B1	datain_b[71..60]	dataout_b[71..60]
B2	datain_b[59..48]	dataout_b[59..48]
B3	datain_b[47..36]	dataout_b[47..36]
B4	datain_b[35..24]	dataout_b[35..24]
B5	datain_b[23..12]	dataout_b[23..12]
B6	datain_b[11..0]	dataout_b[11..0]
A1	datain_a[71..60]	dataout_a[71..60]
A2	datain_a[59..48]	dataout_a[59..48]
A3	datain_a[47..36]	dataout_a[47..36]
A4	datain_a[35..24]	dataout_a[35..24]
A5	datain_a[23..12]	dataout_a[23..12]
A6	datain_a[11..0]	dataout_a[11..0]

Single-Port Mode

The memory blocks also support single-port mode, used when simultaneous reads and writes are not required. See Figure 2–28. A single block in a memory block can support up to two single-port mode RAM blocks in the M4K RAM blocks if each RAM block is less than or equal to 2K bits in size.

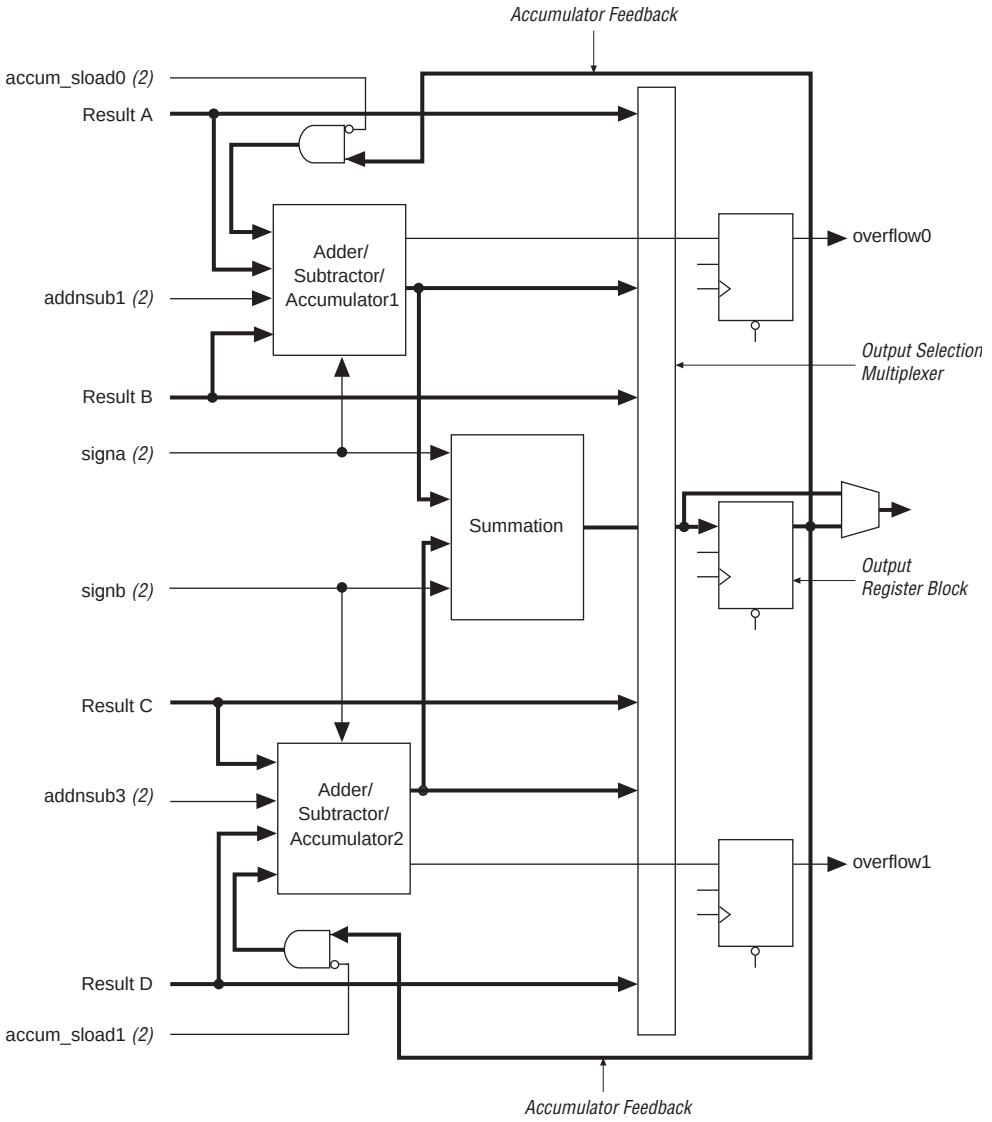
Figure 2–28. Single-Port Mode Note (1)



Note to Figure 2–28:

(1) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Figure 2–34. Adder/Output Blocks *Note (1)*



Notes to Figure 2–34:

(1) Adder/output block shown in Figure 2–34 is in 18 × 18-bit mode. In 9 × 9-bit mode, there are four adder/subtractor blocks and two summation blocks.

(2) These signals are either not registered, registered once, or registered twice to match the data path pipeline.

Adder/Subtractor/Accumulator

The adder/subtractor/accumulator is the first level of the adder/output block and can be used as an accumulator or as an adder/subtractor.

Adder/Subtractor
Each adder/subtractor/accumulator block can perform addition or subtraction using the `addnsub` independent control signal for each first-level adder in 18 × 18-bit mode. There are two `addnsub[1..0]` signals available in a DSP block for any configuration. For 9 × 9-bit mode, one `addnsub[1..0]` signal controls the top two one-level adders and another `addnsub[1..0]` signal controls the bottom two one-level adders. A high `addnsub` signal indicates addition, and a low signal indicates subtraction. The `addnsub` control signal can be unregistered or registered once or twice when feeding the adder blocks to match data path pipelines.

The `signa` and `signb` signals serve the same function as the multiplier block `signa` and `signb` signals. The only difference is that these signals can be registered up to two times. These signals are tied to the same `signa` and `signb` signals from the multiplier and must be connected to the same clocks and control signals.

Accumulator
When configured for accumulation, the adder/output block output feeds back to the accumulator as shown in Figure 2–34. The `accum_sload[1..0]` signal synchronously loads the multiplier result to the accumulator output. This signal can be unregistered or registered once or twice. Additionally, the `overflow` signal indicates the accumulator has overflowed or underflowed in accumulation mode. This signal is always registered and must be externally latched in LEs if the design requires a latched `overflow` signal.

Summation

The output of the adder/subtractor/accumulator block feeds to an optional summation block. This block sums the outputs of the DSP block multipliers. In 9 × 9-bit mode, there are two summation blocks providing the sums of two sets of four 9 × 9-bit multipliers. In 18 × 18-bit mode, there is one summation providing the sum of one set of four 18 × 18-bit multipliers.

bandwidth is tuned by varying the charge pump current, loop filter resistor value, high frequency capacitor value, and *m* counter value. You can manually adjust these values if desired. Bandwidth is programmable from 200 kHz to 1.5 MHz.

External Clock Outputs

Enhanced PLLs 5 and 6 each support up to eight single-ended clock outputs (or four differential pairs). Differential SSTL and HSTL outputs are implemented using 2 single-ended output buffers which are programmed to have opposite polarity. In Quartus II software, simply assign the appropriate differential I/O standard and the software will implement the inversion. See Figure 2–55.

Tables 2–25 and 2–26 show the performance specification for DDR SDRAM, RLDRAM II, QDR SRAM, QDRII SRAM, and ZBT SRAM interfaces in EP1S10 through EP1S40 devices and in EP1S60 and EP1S80 devices. The DDR SDRAM and QDR SRAM numbers in Table 2–25 have been verified with hardware characterization with third-party DDR SDRAM and QDR SRAM devices over temperature and voltage extremes.

Table 2–25. External RAM Support in EP1S10 through EP1S40 Devices

DDR Memory Type	I/O Standard	Maximum Clock Rate (MHz)						
		-5 Speed Grade	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade	
		Flip-Chip	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond
DDR SDRAM *(1)*, *(2)*	SSTL-2	200	167	133	133	100	100	100
DDR SDRAM - side banks *(2)*, *(3)*, *(4)*	SSTL-2	150	133	110	133	100	100	100
RLDRAM II *(4)*	1.8-V HSTL	200	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*
QDR SRAM *(6)*	1.5-V HSTL	167	167	133	133	100	100	100
QDRII SRAM *(6)*	1.5-V HSTL	200	167	133	133	100	100	100
ZBT SRAM *(7)*	LVTTL	200	200	200	167	167	133	133

Notes to Table 2–25:

(1) These maximum clock rates apply if the Stratix device uses DQS phase-shift circuitry to interface with DDR SDRAM. DQS phase-shift circuitry is only available in the top and bottom I/O banks (I/O banks 3, 4, 7, and 8).

(2) For more information on DDR SDRAM, see *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices.*

(3) DDR SDRAM is supported on the Stratix device side I/O banks (I/O banks 1, 2, 5, and 6) without dedicated DQS phase-shift circuitry. The read DQS signal is ignored in this mode.

(4) These performance specifications are preliminary.

(5) This device does not support RLDRAM II.

(6) For more information on QDR or QDRII SRAM, see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

(7) For more information on ZBT SRAM, see *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

Figure 3–5. External Temperature-Sensing Diode

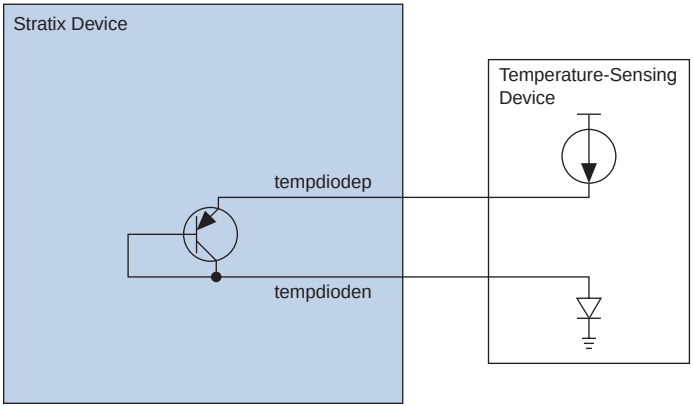


Table 3–6 shows the specifications for bias voltage and current of the Stratix temperature sensing diode.

Table 3–6. Temperature-Sensing Diode Electrical Characteristics

Parameter	Minimum	Typical	Maximum	Unit
I_{BIAS} high	80	100	120	µA
I_{BIAS} low	8	10	12	µA
$V_{BP} - V_{BN}$	0.3		0.9	V
V_{BN}		0.7		V
Series resistance			3	W

Table 4–3. Stratix Device DC Operating Conditions Note (7) (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(9)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(9)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(9)*	60		150	kΩ

Table 4–4. LVTTL Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		1.7	4.1	V
V_{IL}	Low-level input voltage		–0.5	0.7	V
V_{OH}	High-level output voltage	I_{OH} = –4 to –24 mA *(10)*	2.4		V
V_{OL}	Low-level output voltage	I_{OL} = 4 to 24 mA *(10)*		0.45	V

Table 4–5. LVCMOS Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		1.7	4.1	V
V_{IL}	Low-level input voltage		–0.5	0.7	V
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, I_{OH} = –0.1 mA	V_{CCIO} – 0.2		V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, I_{OL} = 0.1 mA		0.2	V

Table 4–6. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Output supply voltage		2.375	2.625	V
V_{IH}	High-level input voltage		1.7	4.1	V
V_{IL}	Low-level input voltage		–0.5	0.7	V
V_{OH}	High-level output voltage	I_{OH} = –1 mA *(10)*	2.0		V
V_{OL}	Low-level output voltage	I_{OL} = 1 mA *(10)*		0.4	V

Table 4–22. SSTL-3 Class I Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.4	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(3)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(3)*			V_{TT} – 0.6	V

Table 4–23. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
$V_{IH(DC)}$	High-level DC input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
$V_{IL(DC)}$	Low-level DC input voltage		–0.3		V_{REF} – 0.2	V
$V_{IH(AC)}$	High-level AC input voltage		V_{REF} + 0.4			V
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.4	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(3)*	V_{TT} + 0.8			V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(3)*			V_{TT} – 0.8	V

Table 4–24. 3.3-V AGP 2× Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		0.39 × V_{CCIO}		0.41 × V_{CCIO}	V
V_{IH}	High-level input voltage *(4)*		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage *(4)*				0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OUT} = –0.5 mA	0.9 × V_{CCIO}		3.6	V
V_{OL}	Low-level output voltage	I_{OUT} = 1.5 mA			0.1 × V_{CCIO}	V

Table 4–25. 3.3-V AGP 1× Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.15	3.3	3.45	V
V_{IH}	High-level input voltage *(4)*		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage *(4)*				0.3 × V_{CCIO}	V

Table 4–41. M4K Block Internal Timing Microparameter Descriptions (Part 2 of 2)

Symbol	Parameter
$t_{M4KDATAAH}$	A port data hold time after clock
$t_{M4KADDRASU}$	A port address setup time before clock
$t_{M4KADDRAH}$	A port address hold time after clock
$t_{M4KDATABSU}$	B port data setup time before clock
$t_{M4KDATABH}$	B port data hold time after clock
$t_{M4KADDRBSU}$	B port address setup time before clock
$t_{M4KADDRBH}$	B port address hold time after clock
$t_{M4KDATACO1}$	Clock-to-output delay when using output registers
$t_{M4KDATACO2}$	Clock-to-output delay without output registers
$t_{M4KCLKHL}$	Register minimum clock high or low time. This is a limit on the min time for the clock on the registers in these blocks. The actual performance is dependent upon the internal point-to-point delays in the blocks and may give slower performance as shown inTable 4–36 on page 4–20 and as reported by the timing analyzer in the Quartus II software.
t_{M4KCLR}	Minimum clear pulse width

Table 4–42. M-RAM Block Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t_{MRAMRC}	Synchronous read cycle time
t_{MRAMWC}	Synchronous write cycle time
$t_{MRAMWERESU}$	Write or read enable setup time before clock
$t_{MRAMWEREH}$	Write or read enable hold time after clock
$t_{MRAMCLKENSU}$	Clock enable setup time before clock
$t_{MRAMCLKENH}$	Clock enable hold time after clock
$t_{MRAMBESU}$	Byte enable setup time before clock
$t_{MRAMBEH}$	Byte enable hold time after clock
$t_{MRAMDATAASU}$	A port data setup time before clock
$t_{MRAMDATAAH}$	A port data hold time after clock
$t_{MRAMADDRASU}$	A port address setup time before clock
$t_{MRAMADDRAH}$	A port address hold time after clock
$t_{MRAMDATABSU}$	B port setup time before clock

Table 4–50. M-RAM Block Internal Timing Microparameters (Part 2 of 2)

Symbol	-5		-6		-7		-8		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{MRAMBESU}$	25		25		28		33		ps
$t_{MRAMBEH}$	18		20		23		27		ps
$t_{MRAMDATAASU}$	25		25		28		33		ps
$t_{MRAMDATAAH}$	18		20		23		27		ps
$t_{MRAMADDRASU}$	25		25		28		33		ps
$t_{MRAMADDRAH}$	18		20		23		27		ps
$t_{MRAMDATABSU}$	25		25		28		33		ps
$t_{MRAMDATABH}$	18		20		23		27		ps
$t_{MRAMADDRBSU}$	25		25		28		33		ps
$t_{MRAMADDRBH}$	18		20		23		27		ps
$t_{MRAMDATACO1}$		1,038		1,053		1,210		1,424	ps
$t_{MRAMDATACO2}$		4,362		4,939		5,678		6,681	ps
$t_{MRAMCLKHL}$	1,000		1,111		1,190		1,400		ps
$t_{MRAMCLR}$	135		150		172		202		ps

Table 4–51. Routing Delay Internal Timing Parameters

Symbol	-5		-6		-7		-8		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{R4}		268		295		339		390	ps
t_{R8}		371		349		401		461	ps
t_{R24}		465		512		588		676	ps
t_{C4}		440		484		557		641	ps
t_{C8}		577		634		730		840	ps
t_{C16}		445		489		563		647	ps
t_{LOCAL}		313		345		396		455	ps

Routing delays vary depending on the load on that specific routing line. The Quartus II software reports the routing delay information when running the timing analysis for a design.

Table 4–104. Stratix I/O Standard Row Pin Input Delay Adders

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
LVCMOS		0		0		0		0	ps
3.3-V LVTTL		0		0		0		0	ps
2.5-V LVTTL		21		22		25		29	ps
1.8-V LVTTL		181		190		218		257	ps
1.5-V LVTTL		300		315		362		426	ps
GTL+		–152		–160		–184		–216	ps
CTT		–168		–177		–203		–239	ps
SSTL-3 Class I		–193		–203		–234		–275	ps
SSTL-3 Class II		–193		–203		–234		–275	ps
SSTL-2 Class I		–262		–276		–317		–373	ps
SSTL-2 Class II		–262		–276		–317		–373	ps
SSTL-18 Class I		–105		–111		–127		–150	ps
SSTL-18 Class II		0		0		0		0	ps
1.5-V HSTL Class I		–151		–159		–183		–215	ps
1.8-V HSTL Class I		–126		–133		–153		–179	ps
LVDS		–149		–157		–180		–212	ps
LVPECL		–149		–157		–180		–212	ps
3.3-V PCML		–65		–69		–79		–93	ps
HyperTransport		77		–81		–93		–110	ps

Tables 4–109 and 4–110 show the adder delays for the column and row IOE programmable delays. These delays are controlled with the Quartus II software logic options listed in the Parameter column.

Table 4–109. Stratix IOE Programmable Delays on Column Pins *Note (1)*

Parameter	Setting	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Decrease input delay to internal cells	Off		3,970		4,367		5,022		5,908	ps
	Small		3,390		3,729		4,288		5,045	ps
	Medium		2,810		3,091		3,554		4,181	ps
	Large		224		235		270		318	ps
	On		224		235		270		318	ps
Decrease input delay to input register	Off		3,900		4,290		4,933		5,804	ps
	On		0		0		0		0	ps
Decrease input delay to output register	Off		1,240		1,364		1,568		1,845	ps
	On		0		0		0		0	ps
Increase delay to output pin	Off		0		0		0		0	ps
	On		397		417		417		417	ps
Increase delay to output enable pin	Off		0		0		0		0	ps
	On		338		372		427		503	ps
Increase output clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase input clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase output enable clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase t_{ZX} delay to output pin	Off		0		0		0		0	ps
	On		2,199		2,309		2,309		2,309	ps

Table 4–110. Stratix IOE Programmable Delays on Row Pins Note (1)

Parameter	Setting	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Decrease input delay to internal cells	Off		3,970		4,367		5,022		5,908	ps
	Small		3,390		3,729		4,288		5,045	ps
	Medium		2,810		3,091		3,554		4,181	ps
	Large		173		181		208		245	ps
	On		173		181		208		245	ps
Decrease input delay to input register	Off		3,900		4,290		4,933		5,804	ps
	On		0		0		0		0	ps
Decrease input delay to output register	Off		1,240		1,364		1,568		1,845	ps
	On		0		0		0		0	ps
Increase delay to output pin	Off		0		0		0		0	ps
	On		397		417		417		417	ps
Increase delay to output enable pin	Off		0		0		0		0	ps
	On		348		383		441		518	ps
Increase output clock enable delay	Off		0		0		0		0	ps
	Small		180		198		227		267	ps
	Large		260		286		328		386	ps
	On		260		286		328		386	ps
Increase input clock enable delay	Off		0		0		0		0	ps
	Small		180		198		227		267	ps
	Large		260		286		328		386	ps
	On		260		286		328		386	ps
Increase output enable clock enable delay	Off		0		0		0		0	ps
	Small		540		594		683		804	ps
	Large		1,016		1,118		1,285		1,512	ps
	On		1,016		1,118		1,285		1,512	ps
Increase t_{ZX} delay to output pin	Off		0		0		0		0	ps
	On		1,993		2,092		2,092		2,092	ps

Note to Table 4–109 and Table 4–110:

(1) The delay chain delays vary for different device densities. These timing values only apply to EP1S30 and EP1S40 devices. Reference the timing information reported by the Quartus II software for other devices.

Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 4 of 4) Notes (1), (2)

Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{DUTY}	LVDS (J = 2 through 10)	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100			100	µs

Notes to Table 4–125:

(1) When J = 4, 7, 8, and 10, the SERDES block is used.

(2) When J = 2 or J = 1, the SERDES is bypassed.

PLL Specifications

Tables 4–127 through 4–129 describe the Stratix device enhanced PLL specifications.

Table 4–127. Enhanced PLL Specifications for -5 Speed Grades (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
f_{IN}	Input clock frequency	3 *(1)*, *(2)*		684	MHz
f_{INPFD}	Input frequency to PFD	3		420	MHz
f_{INDUTY}	Input clock duty cycle	40		60	%
$f_{EINDUTY}$	External feedback clock input duty cycle	40		60	%
$t_{INJITTER}$	Input clock period jitter			±200 *(3)*	ps
$t_{EINJITTER}$	External feedback clock period jitter			±200 *(3)*	ps
t_{FCOMP}	External feedback clock compensation time *(4)*			6	ns
f_{OUT}	Output frequency for internal global or regional clock	0.3		500	MHz
f_{OUT_EXT}	Output frequency for external clock *(3)*	0.3		526	MHz
$t_{OUTDUTY}$	Duty cycle for external clock output (when set to 50%)	45		55	%
t_{JITTER}	Period jitter for external clock output *(6)*			±100 ps for >200-MHz `outclk` ±20 mUI for <200-MHz `outclk`	ps or mUI
$t_{CONFIG5,6}$	Time required to reconfigure the scan chains for PLLs 5 and 6			$289/f_{SCANCLK}$	
$t_{CONFIG11,12}$	Time required to reconfigure the scan chains for PLLs 11 and 12			$193/f_{SCANCLK}$	
$t_{SCANCLK}$	`scanclk` frequency *(5)*			22	MHz
t_{DLOCK}	Time required to lock dynamically (after switchover or reconfiguring any non-post-scale counters/delays) *(7)*			100	µs
t_{LOCK}	Time required to lock from end of device configuration	10		400	µs
f_{VCO}	PLL internal VCO operating range	300		800 *(8)*	MHz
t_{LSKEW}	Clock skew between two external clock outputs driven by the same counter		±50		ps